

Amend the Abstract as follows:

A method of forming a diode having a capacitance below 0.1pF and a breakdown voltage of at least 500V. The diode has method including forming an anode of a first conductivity type and a cathode of a second conductivity type disposed below the anode. At least one of the cathode and anode have multiple, vertically abutting diffusion regions. Forming isolation regions such that the cathode and anode are disposed between and bounded by adjacent isolation regions. The cathode and anode are disposed between and bounded by adjacent isolation regions.

BUR9-2002-0014-US1

Page 3 of 12